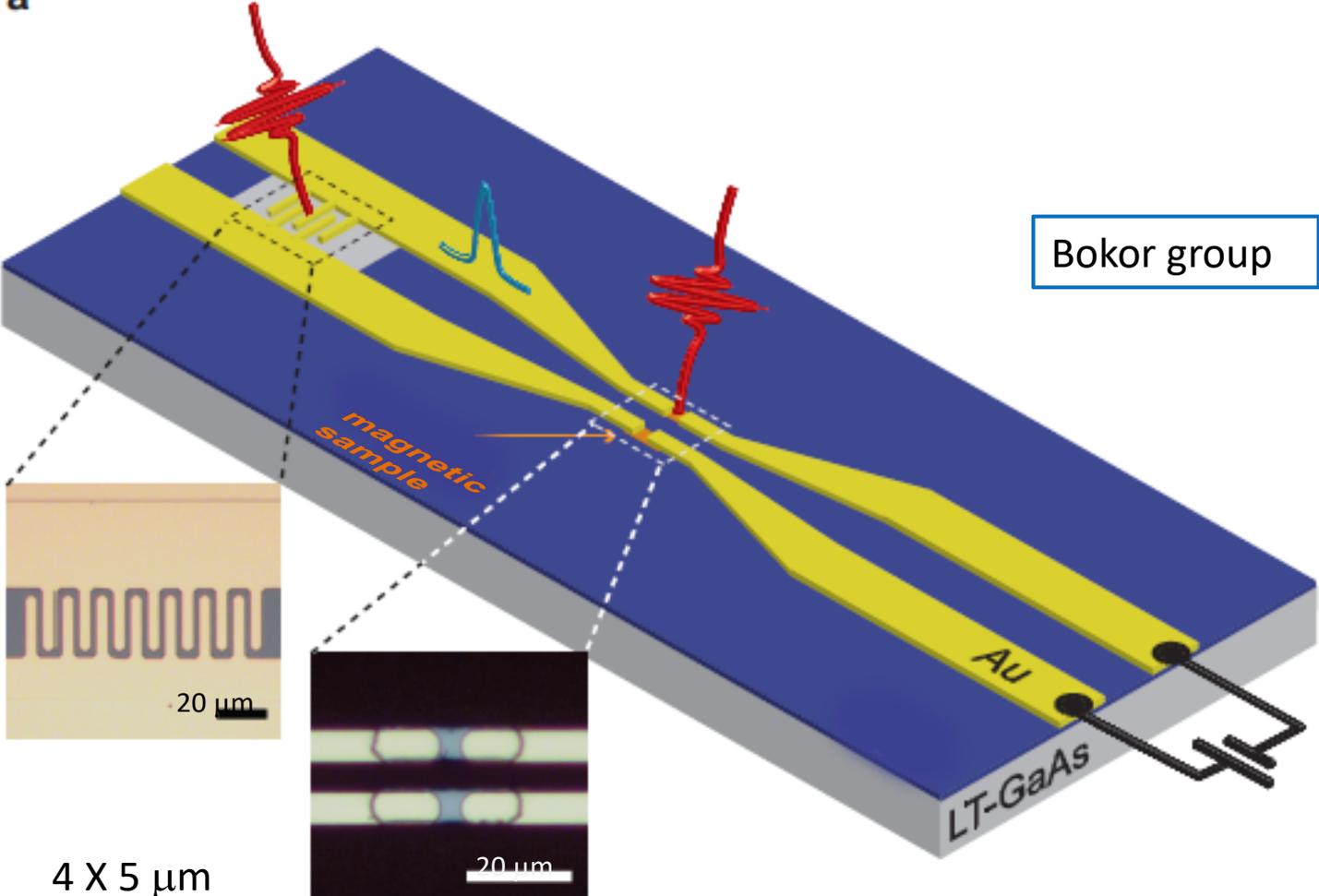
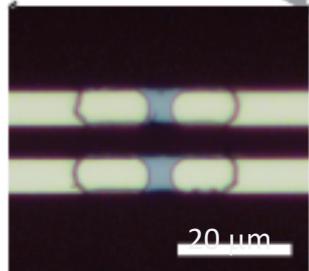
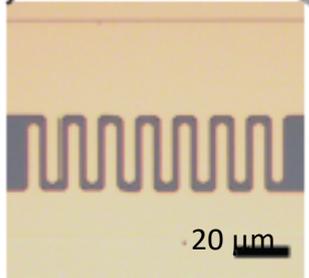


Ultrafast Magnetic Switching

a



Bokor group



4 X 5 μm

Ta(5)/Gd₃₀Fe₆₃Co₇(20)/Pt(5)



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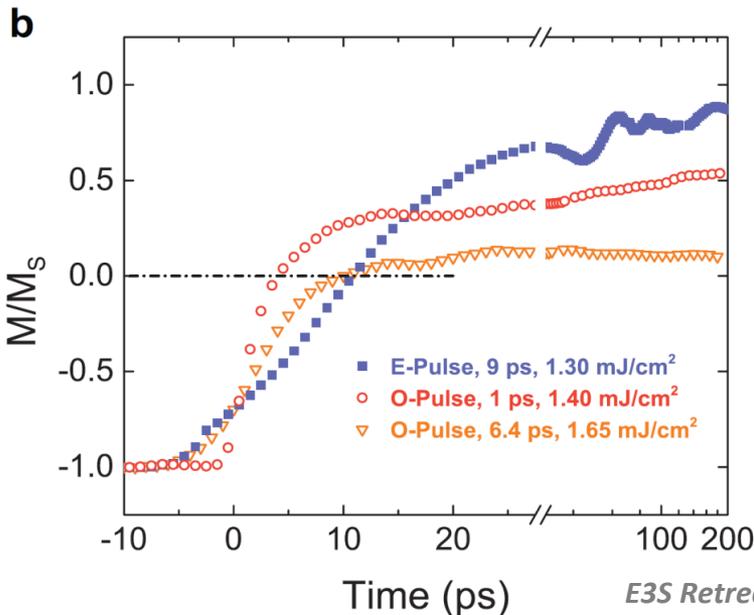
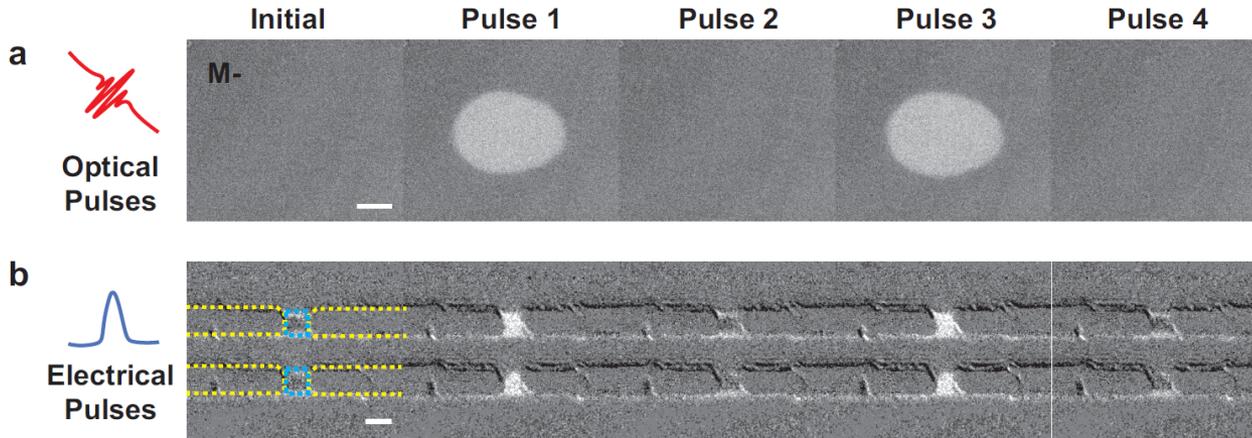
1



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Ultrafast Electrical Switching

Bokor group



- Current density $\sim 7 \times 10^8$ A/cm² (peak)
- Over 10^{10} switching cycles!
- For $(20\text{nm})^3$ cell estimate:
Scaled switching energy $\sim 3.5\text{fJ}$,
switching current $\sim 10\text{s}$ of μA

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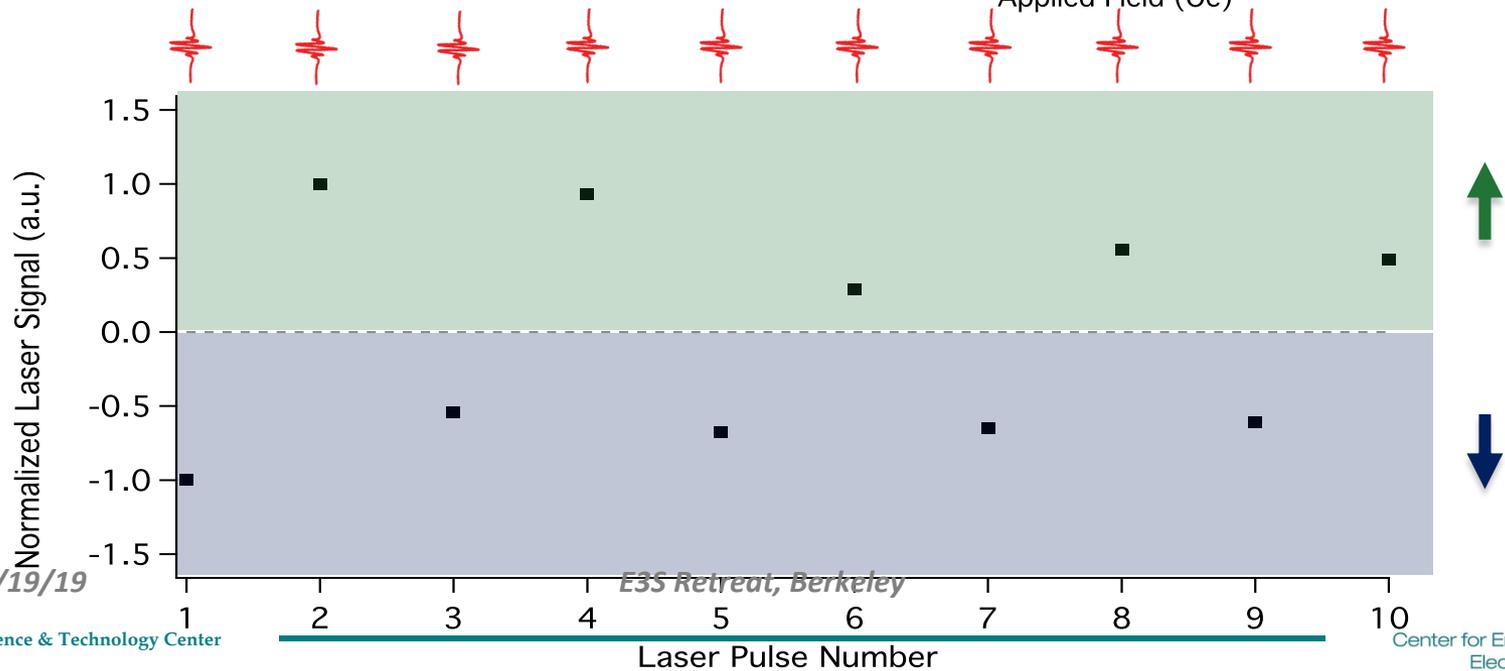
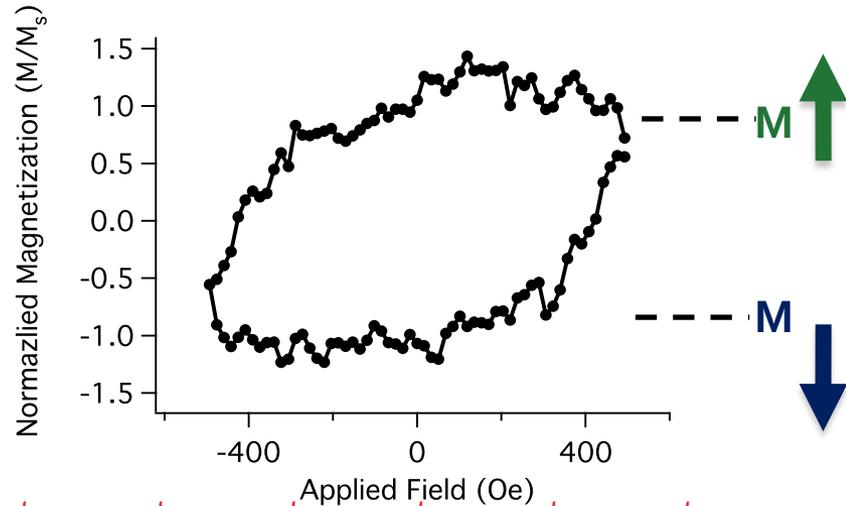
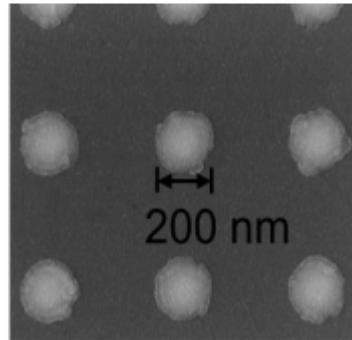


Does switching scale to nano dimensions?

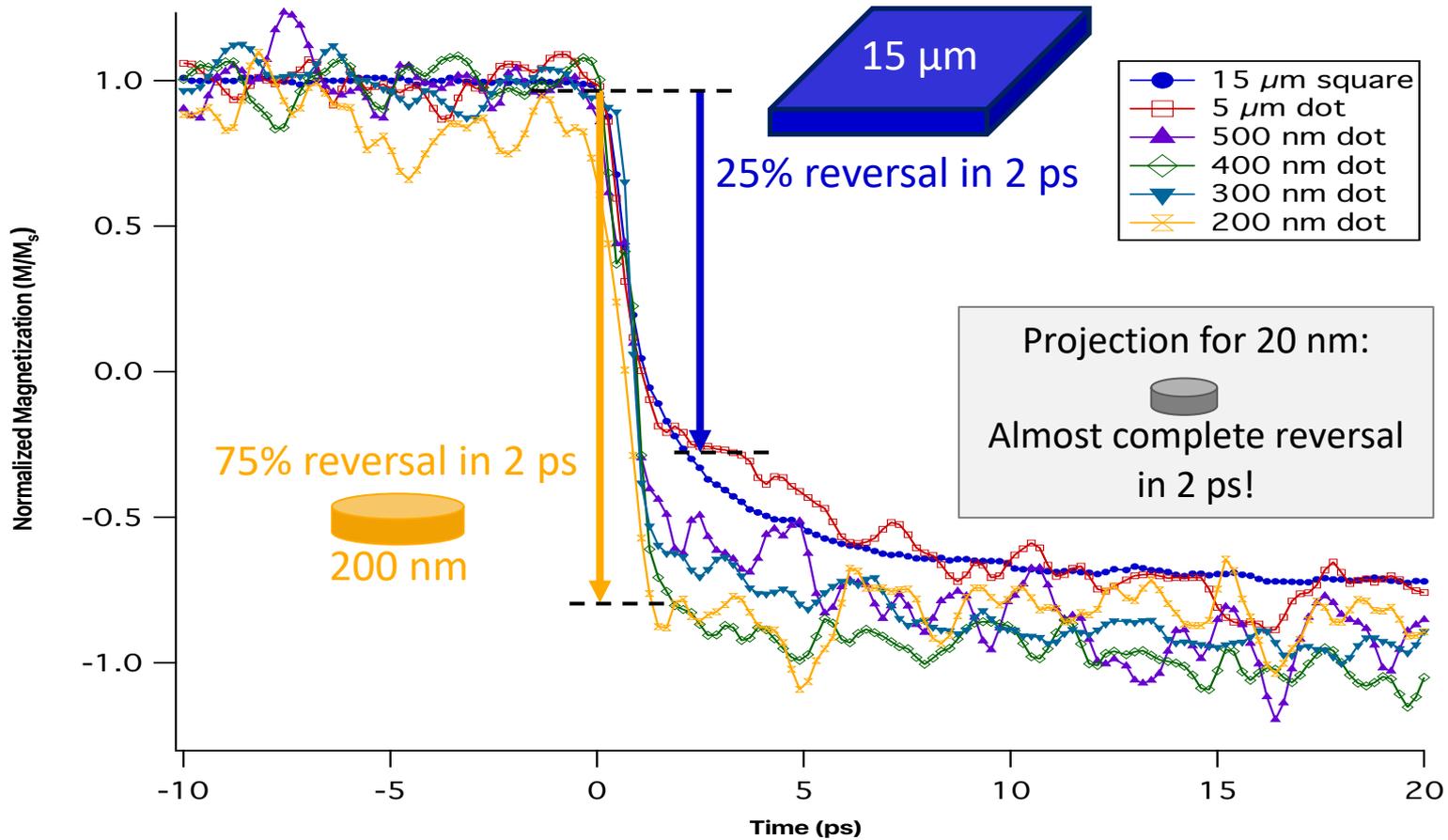


AOS of Nanoscale GdCo Dots

Laser MOKE experiment (200 nm)



Smaller GdCo Dots Switch Faster!



A. El-Ghazaly, et al., APL vol. 114, p. 232407, 2019.

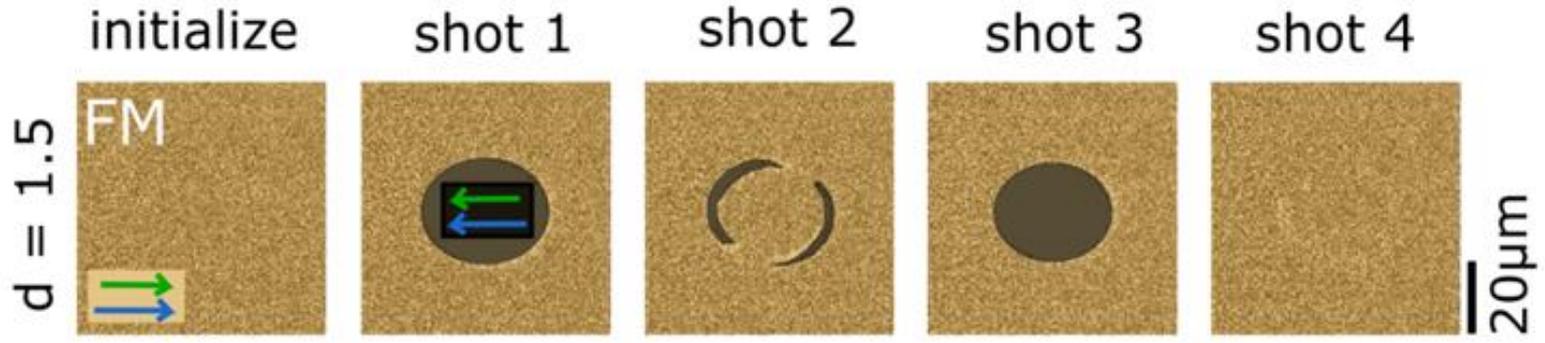
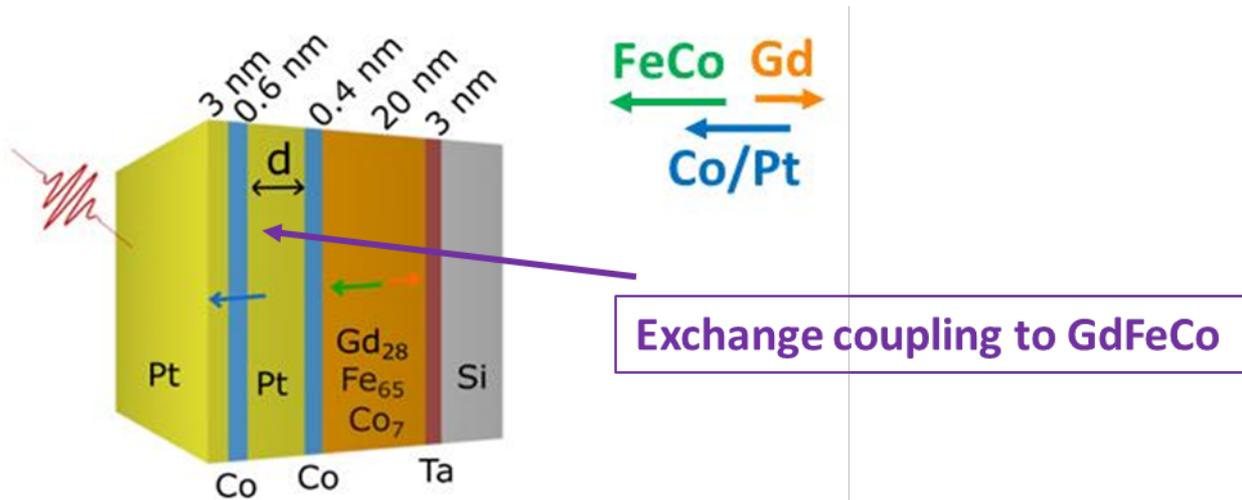
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5



Single-shot all-optical switching of a ferromagnet



Single-Shot switching of Co/Pt!



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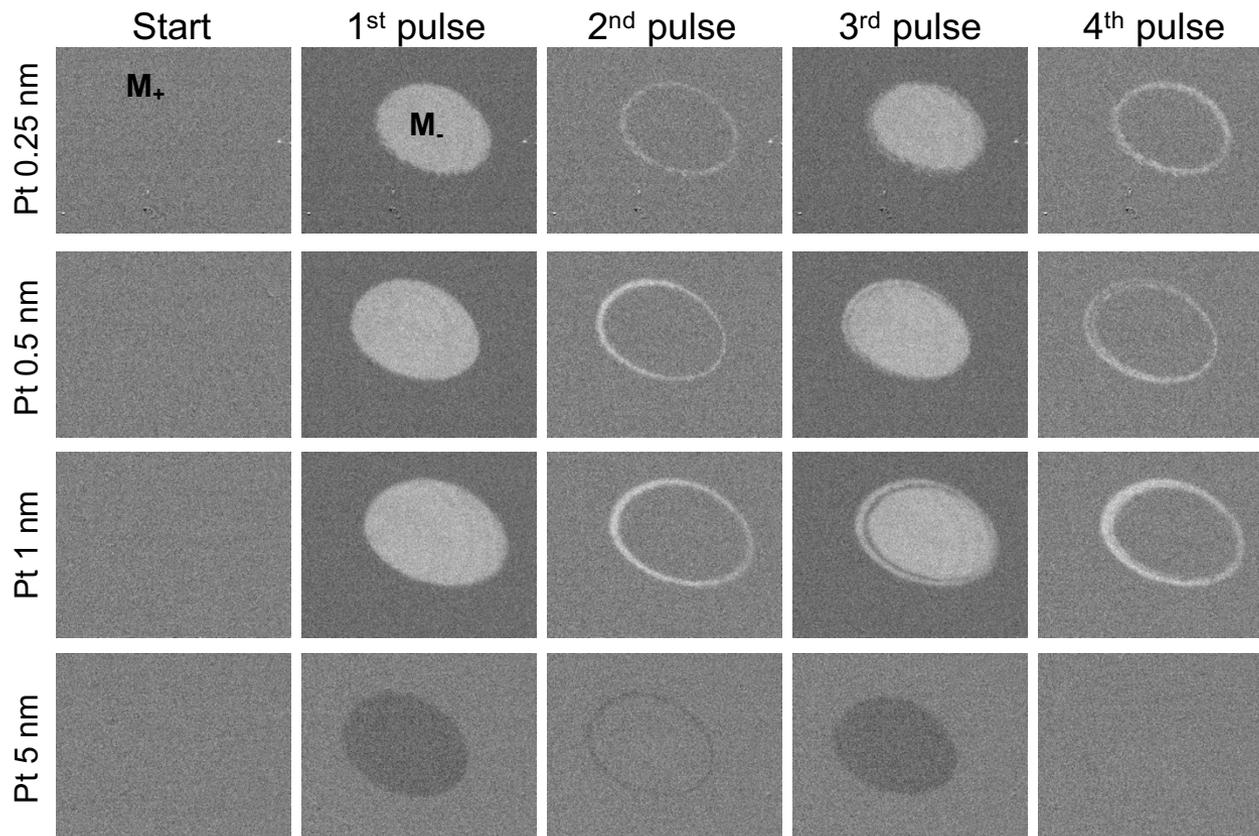
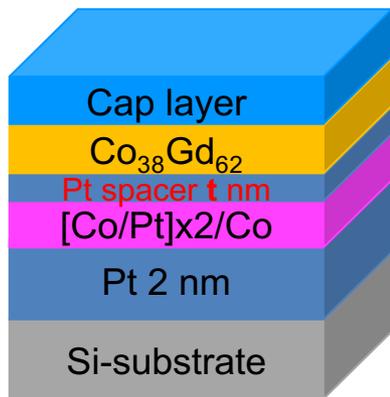
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Co/Pt FM Switching by CoGd



- Co/Pt MLs are ferromagnetically coupled for 0.25, 0.5 and 1 nm Pt spacer thickness
- Exhibits single shot helicity independent all-optical switching (HI-AOS).

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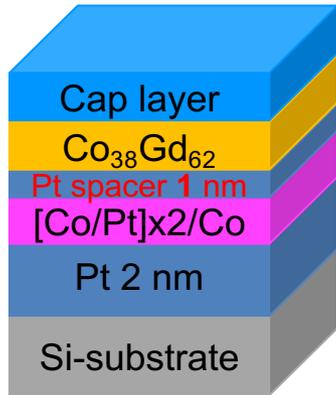
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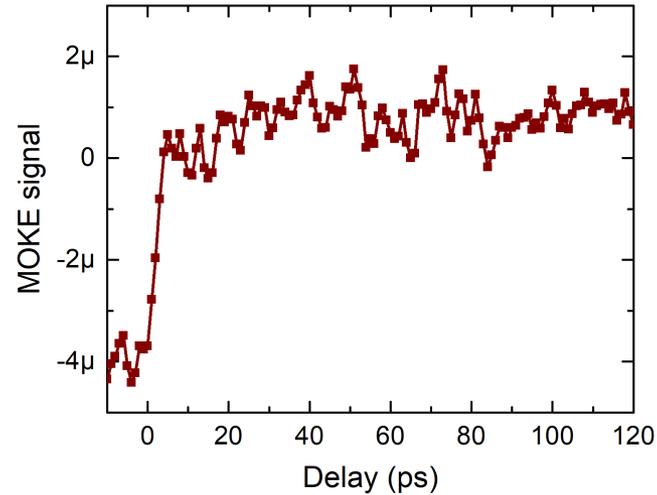
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 Electronics Science

Depth resolved time resolved magnetization dynamics

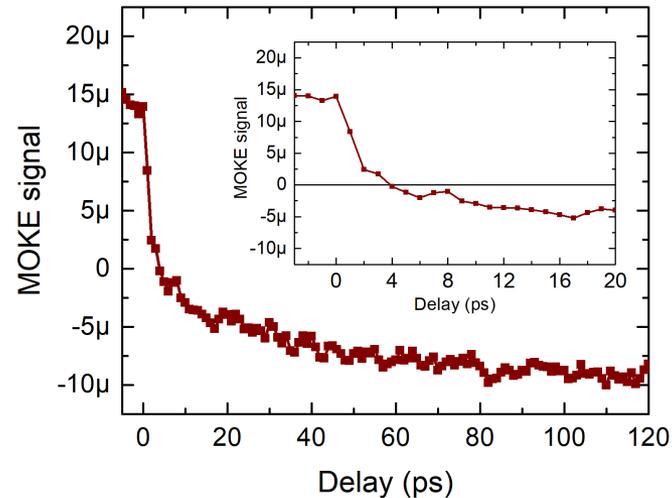
Coupled ferro-ferri sample
Pt spacer 1 nm



CoGd



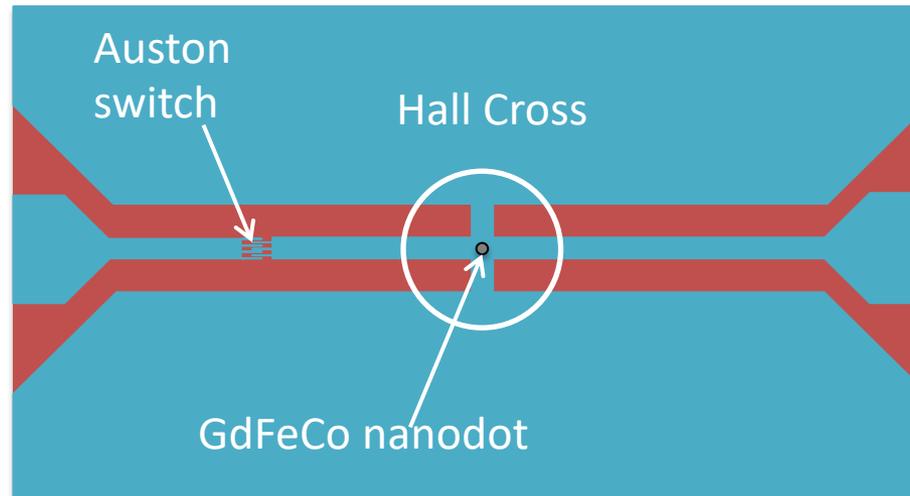
Co/Pt MLs



Magnetization of CoGd and Co/Pt reverses within $\sim 3-4$ ps time scale.



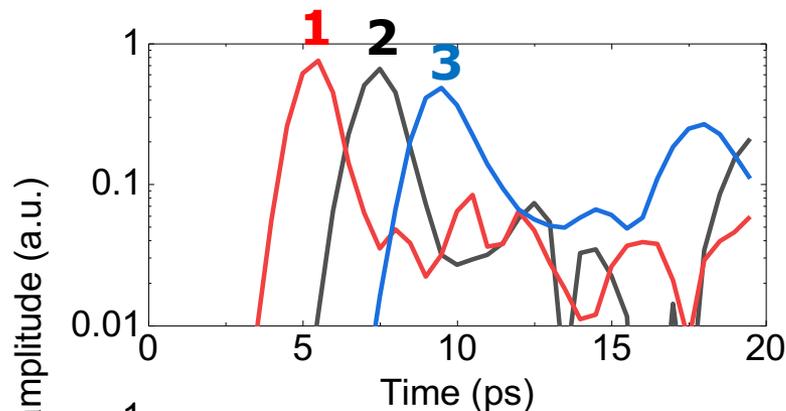
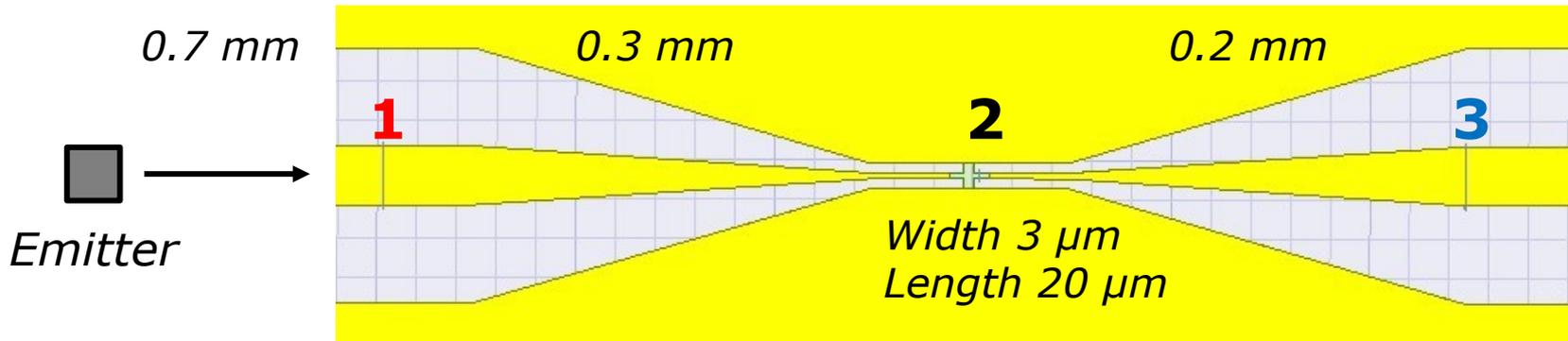
All-Electrical Switching and Readout of GdFeCo Nanodots



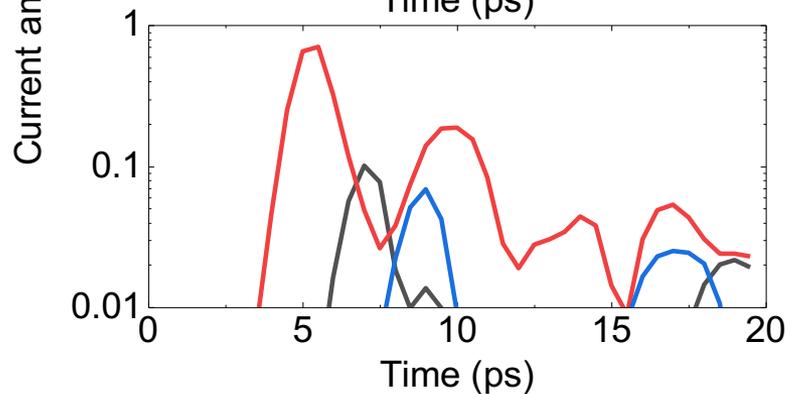
- Fabricate AHE/Transmission Line with Auston switch on LT-GaAs substrate for single GFC dot
- Test magnetization switching using a sub-picosecond electrical current pulse
- Measure electrical resistance after switching using the AHE cross bars



Current propagation in CPW with a Hall bar



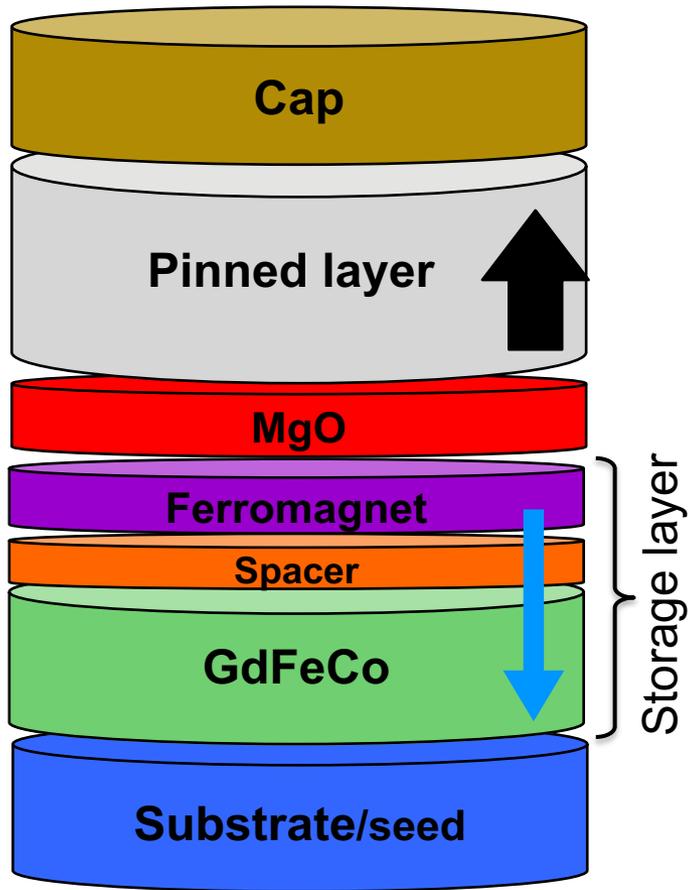
Without a Hall bar
 $I_2/I_1 = 0.88$



With a Hall bar
 $I_2/I_1 = 0.14$



Integrate MTJ Readout



- Ferromagnetic layer coupled with GdFeCo and interfaced with MgO tunnel barrier
- Stack with reasonably high TMR for electrical reading
- Applications: High level cache and non-volatile logic



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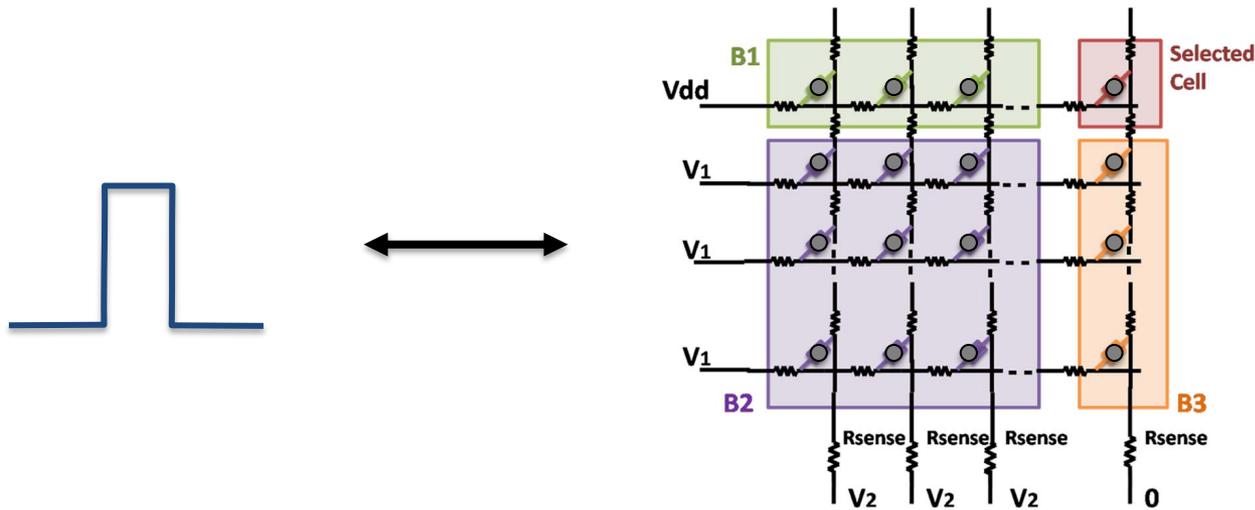
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Full Integration of Ultrafast Memory System

Can it be integrated for minimal current consumption?



Complete integration of GdFeCo nanodot MTJ into CMOS with picosecond pulse generator.

